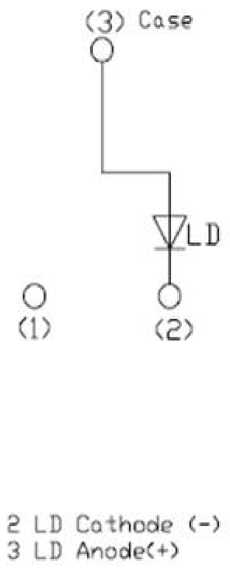
808nm IR Laser Diode
RLD80803001

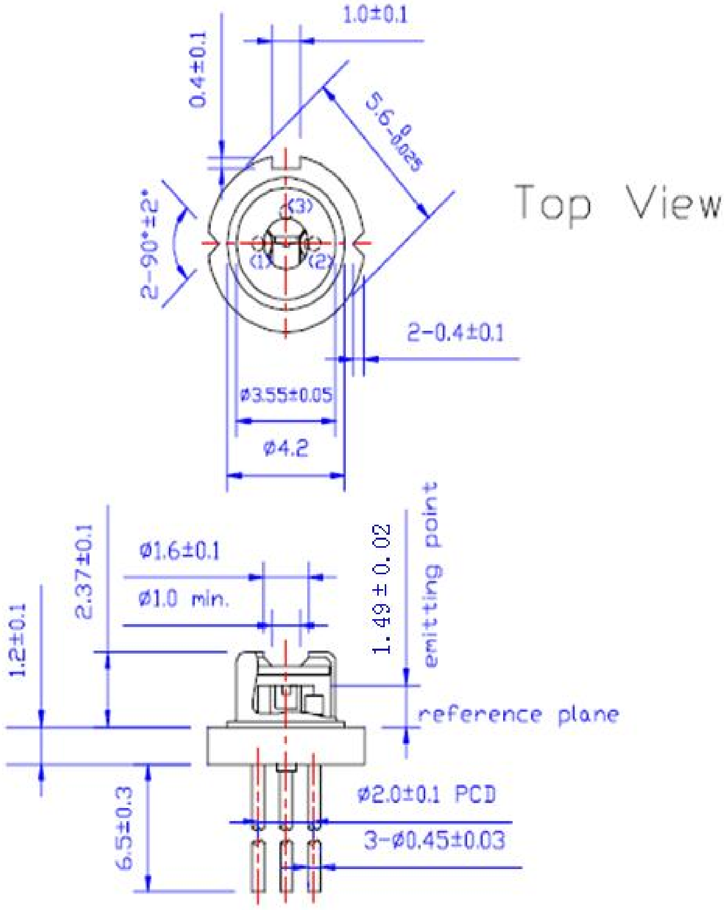
■Specifications

(1) Device: Laser Diode

(2) Structure: TO-18(ϕ 5.6mm)

■External dimensions(Unit : mm)





■Absolute Maximum Ratings(Tc=25℃)

Parameter	Ratings	Unit
Optical Output	300	mW
Operating Temperature	-10 ~ 40	℃
Storage Temperature	-40 ~ 85	℃
Soldering temperature	260	℃

Absolute Maximum Ratings(Tc=25℃)

Operation*	***Symbol***	***Min.***	***Typ.***	***Max.***	***Unit***
Center Wavelength (cw)	λ_C	805	808	811	nm nm
Spectral Width (FWHM)	$\Delta\lambda$	—	3	4	nm
CW Output Power	P_{op}	—	300	—	mW
Fast Axis Divergence（FWHM)	$\theta_\perp$	—	38	45	°
Slow Axis Divergence (FWHM)	$\theta_{//}$	—	10	12	°
Slope Efficiency $P_{op}/(I_{op}-I_{th})$	η	1	1.1	—	W/A
Threshold Current	Ith	—	60	80	mA
Operating Current	I_{op}	—	330	360	mA
Operating Voltage	V_{op}	—	1.8	2.0	V
EO Conversion Efficiency $P_{op}/(I_{op}V_{op})$	η_{tot}	45	50	—	%
Wavelength Temperature Coefficient	／	—	0.3	—	nm/°C
Operating Temperature	T	—	-10～+40	—	℃
Storage Temperature	T_{st}	—	-40～+85	—	℃